

### **Amendments to the Claims:**

There are no amendments to the claims. The following is a listing of the claims as presently pending after last entered amendment.

1. (Previously Presented): A method of depositing a silicon dioxide-comprising layer in the fabrication of integrated circuitry, comprising:

flowing an aluminum-containing organic precursor to a chamber containing a semiconductor substrate effective to deposit an aluminum-comprising layer over the substrate;

flowing an alkoxysilanol to the substrate comprising the aluminum-comprising layer within the chamber effective to deposit a silicon dioxide-comprising layer over the substrate; and

providing at least one halogen within the chamber during at least one of the aluminum-containing organic precursor flowing and the alkoxysilanol flowing under conditions effective to reduce rate of the deposit of the silicon dioxide-comprising layer over the substrate than would otherwise occur under identical conditions but for providing the at least one halogen.

2. (Previously Presented): The method of claim 1 wherein the aluminum-containing organic precursor comprises a methyl aluminum.

3. (Previously Presented): The method of claim 1 wherein the aluminum-comprising layer comprises an aluminum compound.

4. (Original): The method of claim 3 wherein the aluminum compound comprises a methyl aluminum.

5. (Original): The method of claim 3 wherein the aluminum compound comprises an aluminum oxide.

6. (Original): The method of claim 3 wherein the aluminum compound comprises a methyl aluminum oxide.

7. (Previously Presented): The method of claim 1 wherein the aluminum-comprising layer is no more than 3 monolayers thick.

8. (Original): The method of claim 1 wherein the alkoxysilanol comprises tris(tert)butoxysilanol.

9. (Original): The method of claim 1 wherein the alkoxysilanol comprises tris(tert)pentoxysilanol.

10. (Original): The method of claim 1 wherein the halogen is provided during the alkoxysilanol flowing.

11. (Previously Presented): The method of claim 1 wherein the halogen is provided by flowing a halogen-containing precursor to the chamber while flowing the alkoxysilanol.

12. (Original): The method of claim 1 wherein the halogen is provided from deposited material on the substrate which contains the halogen.

13. (Previously Presented): The method of claim 1 wherein the silicon dioxide-comprising layer is formed in a blanketing manner on the substrate.

14. (Previously Presented): The method of claim 1 wherein the silicon dioxide-comprising layer is selectively formed on some areas of the substrate versus other areas of the substrate.

15. (Original): The method of claim 1 wherein said flowing of alkoxysilanol is continuous.

16. (Original): The method of claim 1 wherein said flowing of alkoxysilanol is continuous at a substantially constant rate.

17. (Original): The method of claim 1 wherein said flowing of alkoxysilanol is pulsed.

18. (Original): The method of claim 1 wherein the halogen comprises fluorine.

19. (Original): The method of claim 1 wherein the halogen comprises chlorine.

20. (Original): The method of claim 1 wherein the halogen comprises bromine.

21. (Original): The method of claim 1 wherein the halogen comprises iodine.

Claims 22-99 (Canceled).